

## **isc Silicon NPN Power Transistor**

2SC5404

### **DESCRIPTION**

- · High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- · High Switching Speed
- · Low Saturation Voltage
- · Built-in Damper Diode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

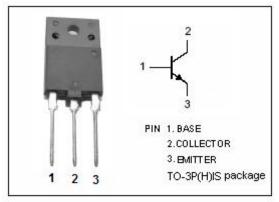
### **APPLICATIONS**

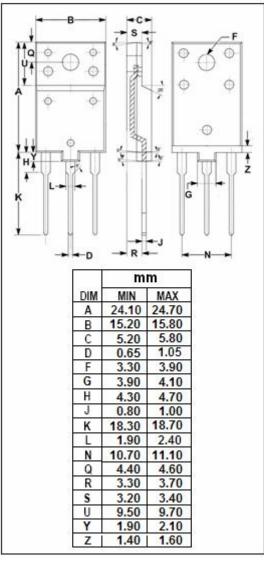
 Horizontal output applications for medium resolution display & color TV.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	600	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current- Continuous	0	А
Ісм	Collector Current- Continuous	18	А
I <sub>B</sub>	Base Current- Continuous	4.5	А
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	50	W
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C

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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.25A			3.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.25A			1.5	V			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1.0	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	uA			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	10		40				
h <sub>FE-2</sub>	DC Current Gain	Ic= 7A; Vc== 5V	4		8				
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		2.5		MHz			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		115		pF			
Switching Times									
t <sub>stg</sub>	Storage Time	$I_{CP}$ = 5.5A; $I_{B1}$ = 1.1A $R_L$ = 64K $Ω$			3.5	μS			
t <sub>f</sub>	Fall Time				0.3	μ <b>s</b>			

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